

IN THE CLAIMS:

Please amend claims 1 and 34 as presented below.

Claims 1-12 (canceled).

13. (Currently Amended) A semiconductor device, comprising:

a semiconductor layer;

an MOS transistor formed on the semiconductor layer;

a resistive conductive layer formed on the semiconductor layer, said resistive conductive layer has a center part and two ends;

a silicon nitride layer or a silicon oxynitride layer formed on the resistive conductive layer; [[and]]

a silicon oxide layer formed on the side of the resistive layer,

wherein widths of said two ends of said resistive conductive layers are wider than a width of said center part of said resistive conductive layer.

Claims 14-16 (canceled).

17. (Previously Presented) The semiconductor device according claim 13, wherein a high breakdown voltage transistor and a low

breakdown voltage transistor of insulated gate types are formed on the semiconductor layer, the high breakdown voltage transistor including a proof voltage between a source and a drain which is different from that of the low breakdown voltage transistor, and wherein the MOS transistor comprises the high breakdown voltage transistor.

Claims 18-33 (canceled).

34. (Currently Amended) A semiconductor device, comprising:
a semiconductor layer;
an MOS transistor formed on the semiconductor layer;
a resistive conductive layer formed on the semiconductor layer,
said resistive conductive layer has a center part and two ends;
a protective layer formed on the resistive conductive layer; and
an insulating layer formed on the side of the resistive layer,
wherein widths of said two ends of said resistive conductive layer
are wider than a width of said center part of said resistive conductive
layer.